

Amendments to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

Listing of Claims:

1-6 (Canceled)

7. (New) A method for manufacturing a display device comprising:  
forming a first semiconductor layer in an active matrix circuit region over a substrate;  
forming a second semiconductor layer in a driver circuit region over the substrate;  
forming a third semiconductor layer over the substrate; and  
forming an insulating film on the first through the third semiconductor layers,  
wherein the third semiconductor layer has a larger width than that of the first and the  
second semiconductor layers,  
wherein the second semiconductor layer is located between the first semiconductor layer  
and the third semiconductor layer, and  
wherein the first through the third semiconductor layers are formed simultaneously.

8. (New) A method for manufacturing a display device according to claim 7, wherein the  
first through the third semiconductor layers are crystalline silicon layers.

9. (New) A method for manufacturing a display device according to claim 7, further  
comprising a step of forming an electrode over each of the first through the third semiconductor  
layers.

10. (New) A method for manufacturing a display device according to claim 7, wherein  
the third semiconductor layer is an electrode for forming a protective capacitor.

11. (New) A method for manufacturing a display device according to claim 7, wherein the display device is a liquid crystal display device.

12. (New) A method for manufacturing a display device comprising:  
forming a first semiconductor layer in an active matrix circuit region over a substrate;  
forming a second semiconductor layer in a driver circuit region over the substrate;  
forming a third semiconductor layer over the substrate;  
forming an insulating film on the first through the third semiconductor layers; and  
introducing an impurity element into portions of the first through the third semiconductor layers,

wherein the second semiconductor layer is located between the first semiconductor layer and the third semiconductor layer, and

wherein the first through the third semiconductor layers are formed simultaneously.

13. (New) A method of manufacturing a display device according to claim 12, wherein the first through the third semiconductor layers are crystalline silicon layers.

14. (New) A method for manufacturing a display device according to claim 12, further comprising a step of forming an electrode over each of the first through the third semiconductor layers.

15. (New) A method for manufacturing a display device according to claim 12, wherein the third semiconductor layer is an electrode for forming a protective capacitor.

16. (New) A method for manufacturing a display device according to claim 12, wherein the display device is a liquid crystal display device.

17. (New) A method for manufacturing a display device comprising:  
forming a first electrode in an active matrix circuit region over a substrate;  
forming a second electrode in a driver circuit region over the substrate;  
forming a third electrode over the substrate, wherein the third electrode surrounds the active matrix circuit region and the driver circuit region, and wherein the first through the third electrodes are electrically connected with each other; and  
electrically separating the third electrode from the first and the second electrodes.

18. (New) A method for manufacturing a display device according to claim 17, wherein the first through the third electrodes comprise aluminum.

19. (New) A method for manufacturing a display device according to claim 17, wherein the third electrode is an electrode for forming a protective capacitor.

20. (New) A method for manufacturing a display device according to claim 17, wherein the display device is a liquid crystal display device.

21. (New) A method for manufacturing a display device comprising:  
forming a first electrode in an active matrix circuit region over a substrate;  
forming a second electrode in a driver circuit region over the substrate;  
forming a third electrode over the substrate, wherein the third electrode surrounds the active matrix circuit region and the driver circuit region, wherein the first through the third electrodes are on a same layer, and wherein the first through the third electrodes are electrically connected with each other; and  
electrically separating the third electrode from the first and the second electrodes.

22. (New) A method for manufacturing a display device according to claim 21, wherein the first through the third electrodes comprise aluminum.

23. (New) A method for manufacturing a display device according to claim 21, wherein the third electrode is an electrode for forming a protective capacitor.

24. (New) A method for manufacturing a display device according to claim 21, wherein the display device is a liquid crystal display device.

25. (New) A method for manufacturing a display device comprising:  
forming a first electrode in an active matrix circuit region over a substrate;  
forming a second electrode in a driver circuit region over the substrate;  
forming a third electrode over the substrate, wherein the third electrode surrounds the active matrix circuit region and the driver circuit region, wherein the third electrode has a larger width than that of the first and the second electrodes, and wherein the first through the third electrodes are electrically connected with each other; and  
electrically separating the third electrode from the first and the second electrodes.

26. (New) A method for manufacturing a display device according to claim 25, wherein the first through the third electrodes comprise aluminum.

27. (New) A method for manufacturing a display device according to claim 25, wherein the third electrode is an electrode for forming a protective capacitor.

28. (New) A method for manufacturing a display device according to claim 25, wherein the display device is a liquid crystal display device.